

Notice of References Cited	Application/Control No. 09/852,999	Applicant(s)/Patent Under Reexamination MEILING ET AL.	
	Examiner Steven H. Rao	Art Unit 2814	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-5,634,605	06-1997	Rubel et al.	248/228.1
	C	US-5,776,819	07-1998	Mahan et al.	438/482
	D	US-			
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	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

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	U	H. Meiling et al., " Stability of hot-wire deposited amorphous-silicon thin-film transistors, Appl. Phys. Lett. 69(8), 19 August 1996.
	V	Kikuo Ono et al. , " Inverse- Staggered Ploycrystalline Silicon Thin- Film Transisitors Fabricated By Excimer Laser Irradiation, Electronics and Communications in Japan , Part 2, Vol.76, No. 12, 1993 pages 40-47.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.